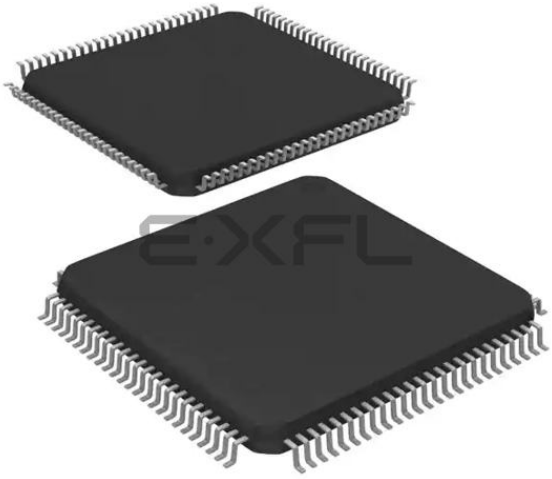

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	EBI/EMI, I²C, IrDA, SmartCard, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	83
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32gg380f512g-e-qfp100r

3 Electrical Characteristics

3.1 Test Conditions

3.1.1 Typical Values

The typical data are based on T_{AMB}=25°C and V_{DD}=3.0 V, as defined in Table 3.2 (p. 10), unless otherwise specified.

3.1.2 Minimum and Maximum Values

The minimum and maximum values represent the worst conditions of ambient temperature, supply voltage and frequencies, as defined in Table 3.2 (p. 10) , unless otherwise specified.

3.2 Absolute Maximum Ratings

The absolute maximum ratings are stress ratings, and functional operation under such conditions are not guaranteed. Stress beyond the limits specified in Table 3.1 (p. 10) may affect the device reliability or cause permanent damage to the device. Functional operating conditions are given in Table 3.2 (p. 10) .

Table 3.1. Absolute Maximum Ratings

Symbol	Parameter	Condition	Min	Typ	Max	Unit
T_{STG}	Storage temperature range		-40		150	°C
T_S	Maximum soldering temperature	Latest IPC/JEDEC J-STD-020 Standard			260	°C
V_{DDMAX}	External main supply voltage		0		3.8	V
V_{IOPIN}	Voltage on any I/O pin		-0.3		V_{DD}+0.3	V
I_{IOMAX}	Current per I/O pin (sink)				100	mA
	Current per I/O pin (source)				-100	mA

3.3 General Operating Conditions

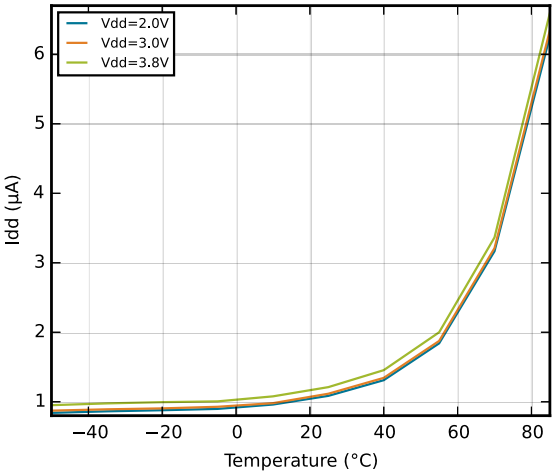
3.3.1 General Operating Conditions

Table 3.2. General Operating Conditions

Symbol	Parameter	Min	Typ	Max	Unit
T_{AMB}	Ambient temperature range	-40		85	°C
V_{DDOP}	Operating supply voltage	1.98		3.8	V
f_{APB}	Internal APB clock frequency			48	MHz
f_{AHB}	Internal AHB clock frequency			48	MHz

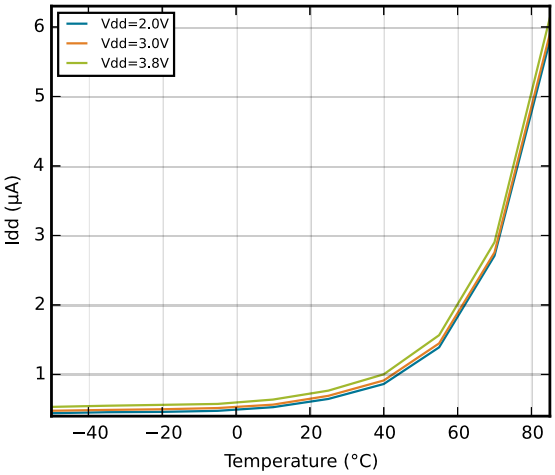
3.4.1 EM2 Current Consumption

Figure 3.1. EM2 current consumption. RTC[1] prescaled to 1 Hz, 32.768 kHz LFRCO.



3.4.2 EM3 Current Consumption

Figure 3.2. EM3 current consumption.

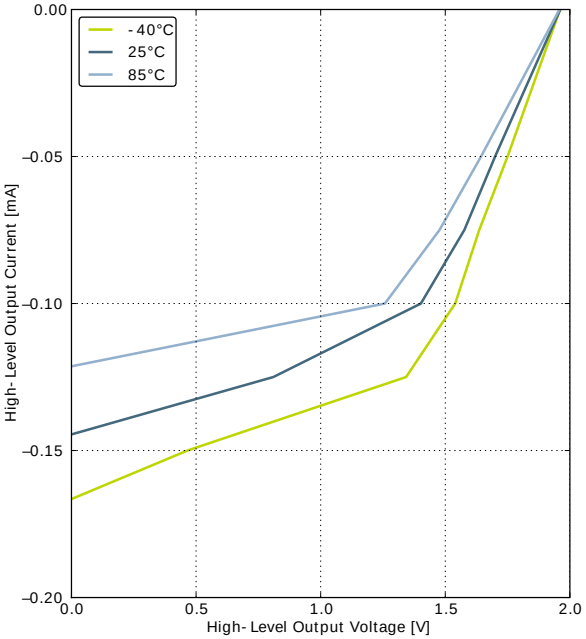


[1]Using backup RTC.

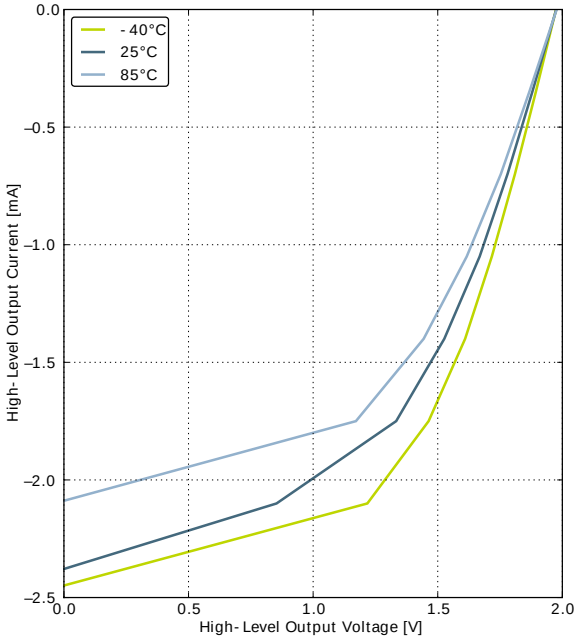
Table 3.5. Power Management

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$V_{BODextthr-}$	BOD threshold on falling external supply voltage	EM0	1.74		1.96	V
		EM2	1.74		1.98	V
$V_{BODintthr-}$	BOD threshold on falling internally regulated supply voltage		1.57		1.70	V
$V_{BODextthr+}$	BOD threshold on rising external supply voltage			1.85	1.98	V
$V_{PORthr+}$	Power-on Reset (POR) threshold on rising external supply voltage				1.98	V
t_{RESET}	Delay from reset is released until program execution starts	Applies to Power-on Reset, Brown-out Reset and pin reset.		163		µs
$C_{DECOUPLE}$	Voltage regulator decoupling capacitor.	X5R capacitor recommended. Apply between DECOUPLE pin and GROUND		1		µF
C_{USB_VREGO}	USB voltage regulator out decoupling capacitor.	X5R capacitor recommended. Apply between USB_VREGO pin and GROUND		1		µF
C_{USB_VREGI}	USB voltage regulator in decoupling capacitor.	X5R capacitor recommended. Apply between USB_VREGI pin and GROUND		4.7		µF

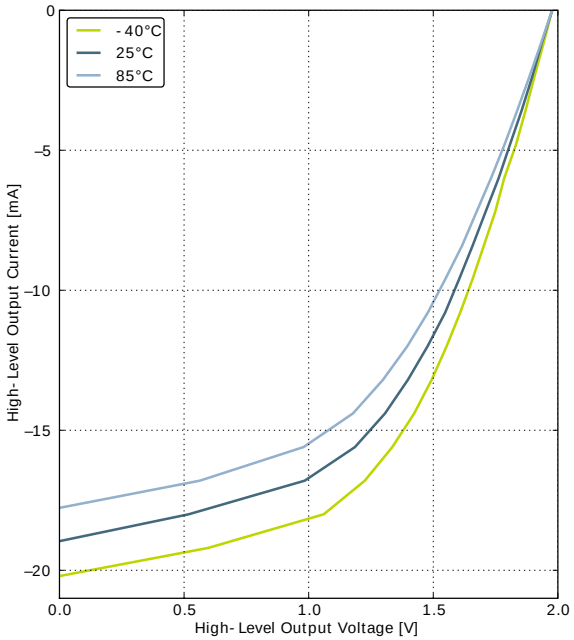
Figure 3.5. Typical High-Level Output Current, 2V Supply Voltage



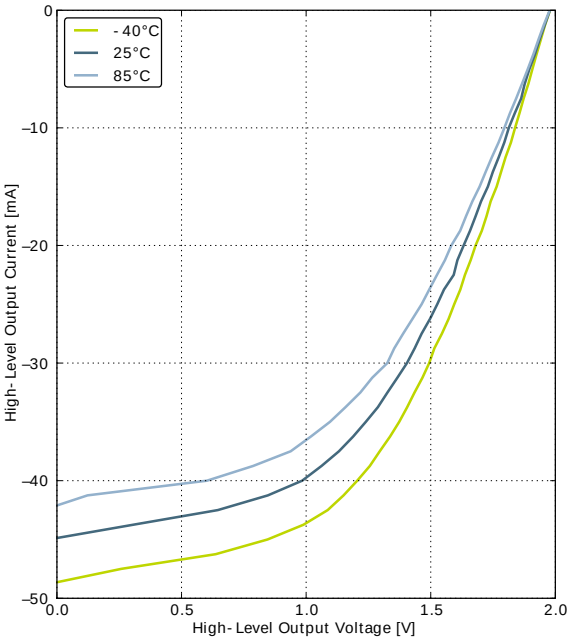
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD



GPIO_Px_CTRL DRIVEMODE = HIGH

3.9 Oscillators

3.9.1 LFXO

Table 3.8. LFXO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{LFXO}	Supported nominal crystal frequency			32.768		kHz
ESR_{LFXO}	Supported crystal equivalent series resistance (ESR)			30	120	kOhm
C_{LFXOL}	Supported crystal external load range		X[1]		25	pF
DC_{LFXO}	Duty cycle		48	50	53.5	%
I_{LFXO}	Current consumption for core and buffer after startup.	ESR=30 kOhm, C_L=10 pF, LFXOBOOST in CMU_CTRL is 1		190		nA
t_{LFXO}	Start- up time.	ESR=30 kOhm, C_L=10 pF, 40% - 60% duty cycle has been reached, LFXOBOOST in CMU_CTRL is 1		400		ms

[1]See Minimum Load Capacitance (C_{LFXOL}) Requirement For Safe Crystal Startup in energyAware Designer in Simplicity Studio

For safe startup of a given crystal, the Configurator tool in Simplicity Studio contains a tool to help users configure both load capacitance and software settings for using the LFXO. For details regarding the crystal configuration, the reader is referred to application note "AN0016 EFM32 Oscillator Design Consideration".

3.9.2 HFXO

Table 3.9. HFXO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{HFXO}	Supported nominal crystal Frequency		4		48	MHz
ESR_{HFXO}	Supported crystal equivalent series resistance (ESR)	Crystal frequency 48 MHz			50	Ohm
		Crystal frequency 32 MHz		30	60	Ohm
		Crystal frequency 4 MHz		400	1500	Ohm
g_{mHFXO}	The transconductance of the HFXO input transistor at crystal startup	HFXOBOOST in CMU_CTRL equals 0b11	20			mS
C_{HFXOL}	Supported crystal external load range		5		25	pF
I_{HFXO}	Current consumption for HFXO after startup	4 MHz: ESR=400 Ohm, C_L=20 pF, HFXOBOOST in CMU_CTRL equals 0b11		85		µA
		32 MHz: ESR=30 Ohm, C_L=10 pF, HFXOBOOST in CMU_CTRL equals 0b11		165		µA
t_{HFXO}	Startup time	32 MHz: ESR=30 Ohm, C_L=10 pF, HFXOBOOST in CMU_CTRL equals 0b11		400		µs

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{HFRCO}	Current consumption (Production test condition = 14MHz)	f_{HFRCO} = 28 MHz		165	190	µA
		f_{HFRCO} = 21 MHz		134	155	µA
		f_{HFRCO} = 14 MHz		106	120	µA
		f_{HFRCO} = 11 MHz		94	110	µA
		f_{HFRCO} = 6.6 MHz		77	90	µA
		f_{HFRCO} = 1.2 MHz		25	32	µA
$TUNESTEP_{H-FRCO}$	Frequency step for LSB change in TUNING value			0.3[3]		%

[1]For devices with prod. rev. < 19, Typ = 7MHz and Min/Max values not applicable.

[2]For devices with prod. rev. < 19, Typ = 1MHz and Min/Max values not applicable.

[3]The TUNING field in the CMU_HFRCOCTRL register may be used to adjust the HFRCO frequency. There is enough adjustment range to ensure that the frequency bands above 7 MHz will always have some overlap across supply voltage and temperature. By using a stable frequency reference such as the LFXO or HFXO, a firmware calibration routine can vary the TUNING bits and the frequency band to maintain the HFRCO frequency at any arbitrary value between 7 MHz and 28 MHz across operating conditions.

Figure 3.11. Calibrated HFRCO 1 MHz Band Frequency vs Supply Voltage and Temperature

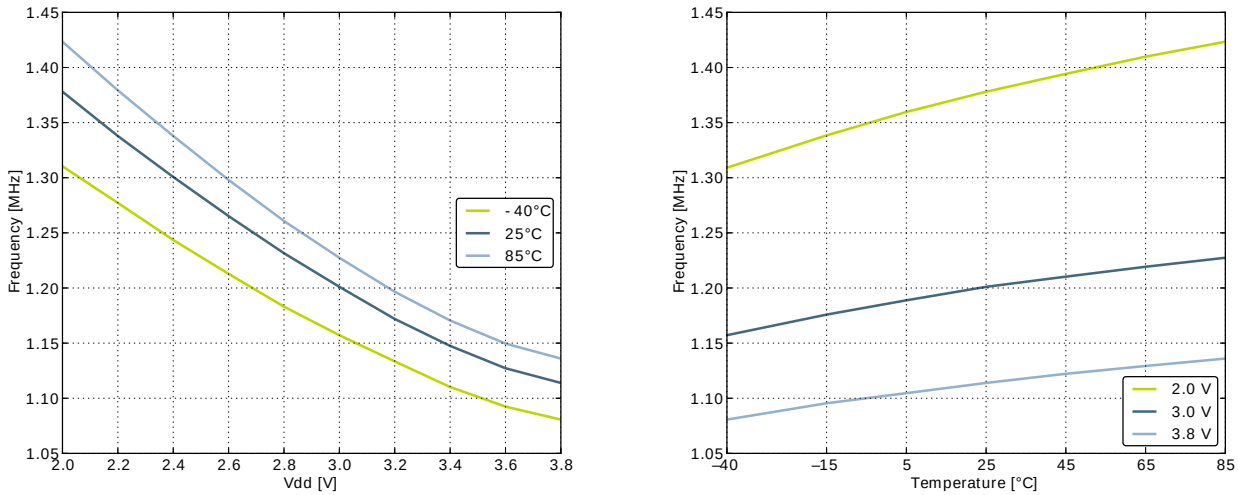
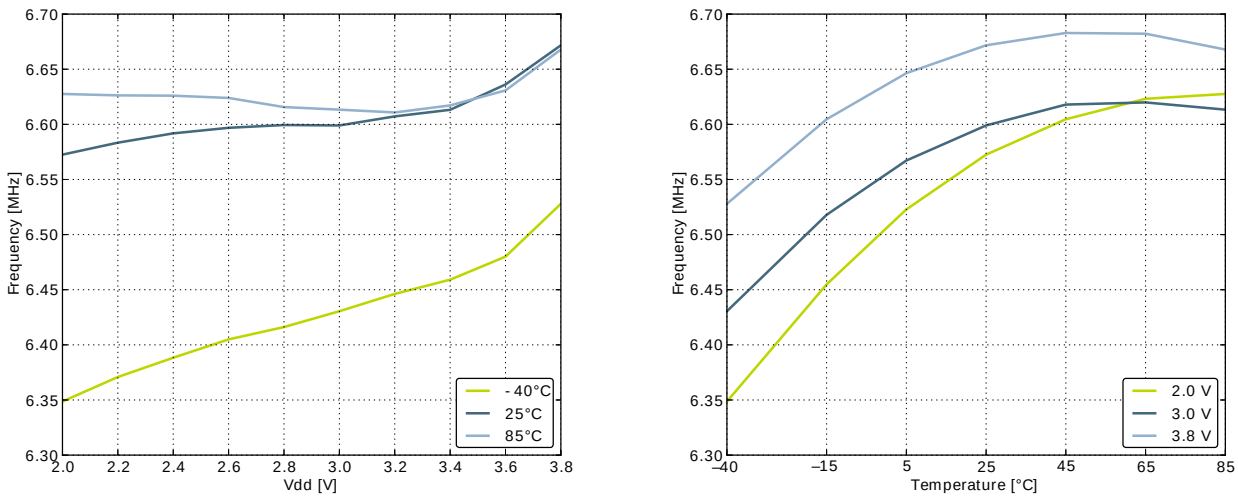


Figure 3.12. Calibrated HFRCO 7 MHz Band Frequency vs Supply Voltage and Temperature



3.9.6 ULFRCO

Table 3.13. ULFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{ULFRCO}	Oscillation frequency	25°C, 3V	0.70		1.75	kHz
TC_{ULFRCO}	Temperature coefficient			0.05		%/°C
VC_{ULFRCO}	Supply voltage coefficient			-18.2		%/V

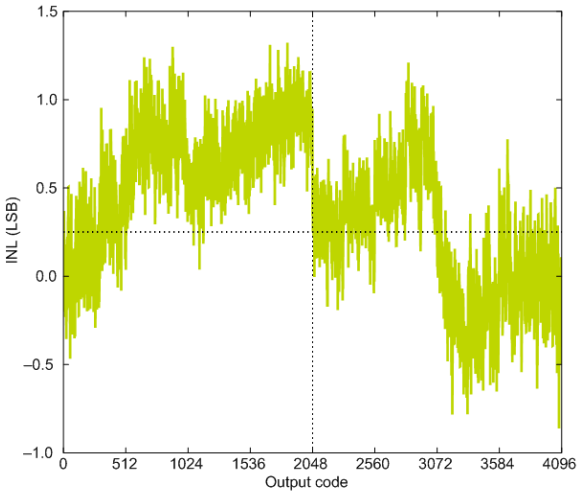
3.10 Analog Digital Converter (ADC)

Table 3.14. ADC

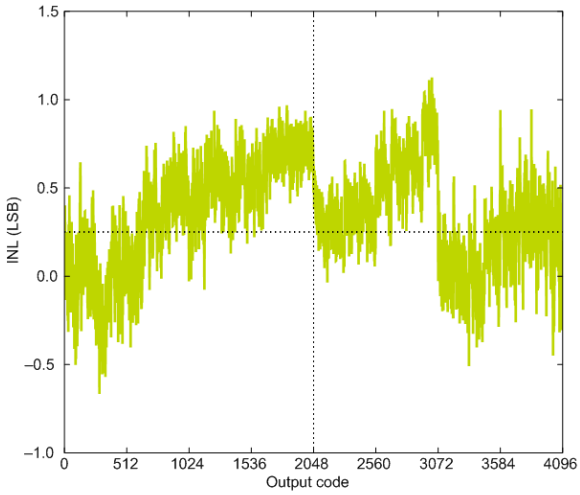
Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{ADCIN}	Input voltage range	Single ended	0		V_{REF}	V
		Differential	$-V_{REF}/2$		$V_{REF}/2$	V
$V_{ADCREFIN}$	Input range of external reference voltage, single ended and differential		1.25		V_{DD}	V
$V_{ADCREFIN\_CH7}$	Input range of external negative reference voltage on channel 7	See $V_{ADCREFIN}$	0		V_{DD} - 1.1	V
$V_{ADCREFIN\_CH6}$	Input range of external positive reference voltage on channel 6	See $V_{ADCREFIN}$	0.625		V_{DD}	V
$V_{ADCCMIN}$	Common mode input range		0		V_{DD}	V
I_{ADCIN}	Input current	2pF sampling capacitors		<100		nA
$CMRR_{ADC}$	Analog input common mode rejection ratio			65		dB
I_{ADC}	Average active current	1 MSamples/s, 12 bit, external reference		351		µA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUPMODE in ADCn_CTRL set to 0b00		67		µA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUPMODE in ADCn_CTRL set to 0b01		63		µA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUPMODE in ADCn_CTRL set to 0b10		64		µA
I_{ADCREF}	Current consumption of internal voltage reference	Internal voltage reference		65		µA

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		62		dB
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		200 kSamples/s, 12 bit, single ended, V_{DD} reference		67		dB
		200 kSamples/s, 12 bit, differential, internal 1.25V reference		63		dB
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		66		dB
		200 kSamples/s, 12 bit, differential, 5V reference		66		dB
		200 kSamples/s, 12 bit, differential, V_{DD} reference	63	66		dB
		200 kSamples/s, 12 bit, differential, 2xV_{DD} reference		70		dB
$SINAD_{ADC}$	SIgnal-to-Noise And Distortion-ratio (SINAD)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		58		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		62		dB
		1 MSamples/s, 12 bit, single ended, V_{DD} reference		64		dB
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		60		dB
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		64		dB
		1 MSamples/s, 12 bit, differential, 5V reference		54		dB
		1 MSamples/s, 12 bit, differential, V_{DD} reference		66		dB
		1 MSamples/s, 12 bit, differential, 2xV_{DD} reference		68		dB
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		61		dB
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		65		dB
		200 kSamples/s, 12 bit, single ended, V_{DD} reference		66		dB
		200 kSamples/s, 12 bit, differential, internal 1.25V reference		63		dB
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		66		dB
		200 kSamples/s, 12 bit, differential, 5V reference		66		dB
		200 kSamples/s, 12 bit, differential, V_{DD} reference	62	65		dB

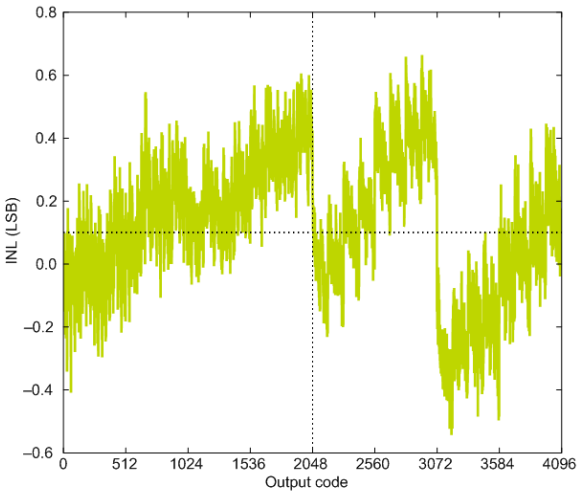
Figure 3.20. ADC Integral Linearity Error vs Code, Vdd = 3V, Temp = 25°C



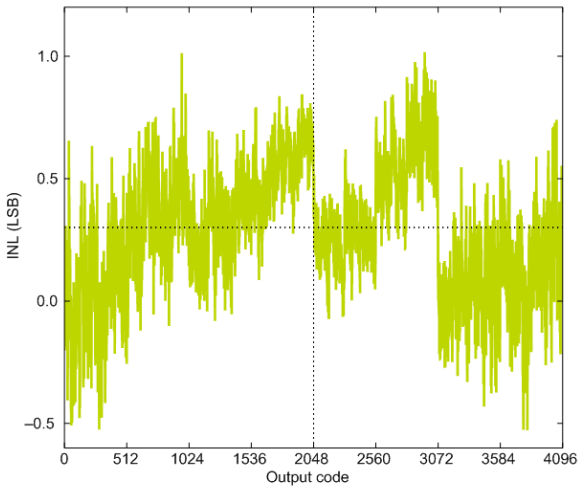
1.25V Reference



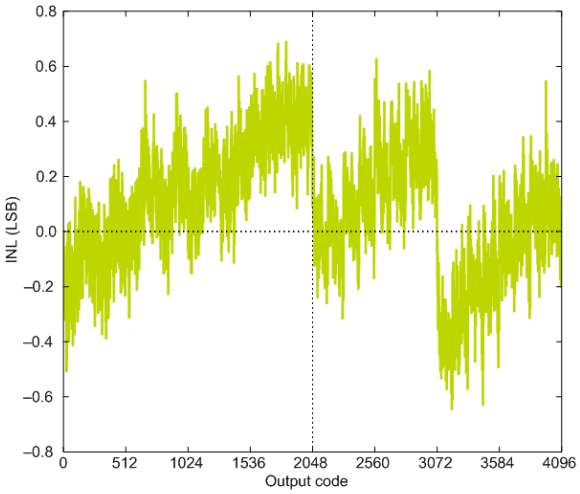
2.5V Reference



2XVDDVSS Reference



5VDIFF Reference



VDD Reference

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1, Unity Gain		13	17	µA
G_{OL}	Open Loop Gain	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		101		dB
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		98		dB
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		91		dB
GBW_{OPAMP}	Gain Bandwidth Product	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		6.1		MHz
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		1.8		MHz
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		0.25		MHz
PM_{OPAMP}	Phase Margin	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0, C_L=75 pF		64		°
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1, C_L=75 pF		58		°
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1, C_L=75 pF		58		°
R_{INPUT}	Input Resistance			100		Mohm
R_{LOAD}	Load Resistance		200			Ohm
I_{LOAD_DC}	DC Load Current				11	mA
V_{INPUT}	Input Voltage	OPAxHCMDIS=0	V_{SS}		V_{DD}	V
		OPAxHCMDIS=1	V_{SS}		V_{DD}-1.2	V
V_{OUTPUT}	Output Voltage		V_{SS}		V_{DD}	V
V_{OFFSET}	Input Offset Voltage	Unity Gain, V_{SS}<V_{in}<V_{DD}, OPAxHCMDIS=0	-13	0	11	mV
		Unity Gain, V_{SS}<V_{in}<V_{DD}-1.2, OPAxHCMDIS=1		1		mV
V_{OFFSET_DRIFT}	Input Offset Voltage Drift				0.02	mV/°C
SR_{OPAMP}	Slew Rate	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		3.2		V/µs
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		0.8		V/µs
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		0.1		V/µs
N_{OPAMP}	Voltage Noise	V_{out}=1V, RESSEL=0, 0.1 Hz<f<10 kHz, OPAx-HCMDIS=0		101		$µV_{RMS}$
		V_{out}=1V, RESSEL=0, 0.1 Hz<f<10 kHz, OPAx-HCMDIS=1		141		$µV_{RMS}$

Figure 3.34. EBI Read Enable Related Timing Requirements

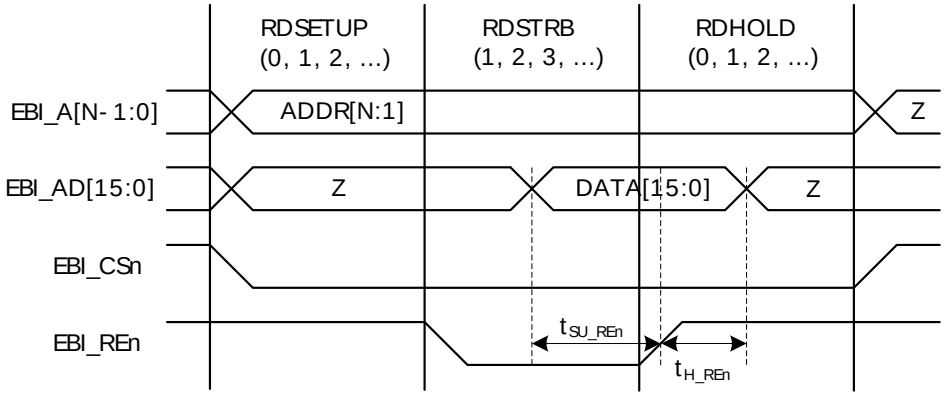


Table 3.22. EBI Read Enable Related Timing Requirements

Symbol	Parameter	Min	Typ	Max	Unit
t_{SU_REn} [1 2 3 4]	Setup time, from EBI_AD valid to trailing EBI_REn edge	37			ns
t_{H_Ren} [1 2 3 4]	Hold time, from trailing EBI_REn edge to EBI_AD invalid	-1			ns

[1]Applies for all addressing modes (figure only shows D16A8).
[2]Applies for both EBI_REn and EBI_NANDREn (figure only shows EBI_REn)
[3]Applies for all polarities (figure only shows active low signals)
[4]Measurement done at 10% and 90% of V_{DD} (figure shows 50% of $_{VDD}$)

Figure 3.35. EBI Ready/Wait Related Timing Requirements

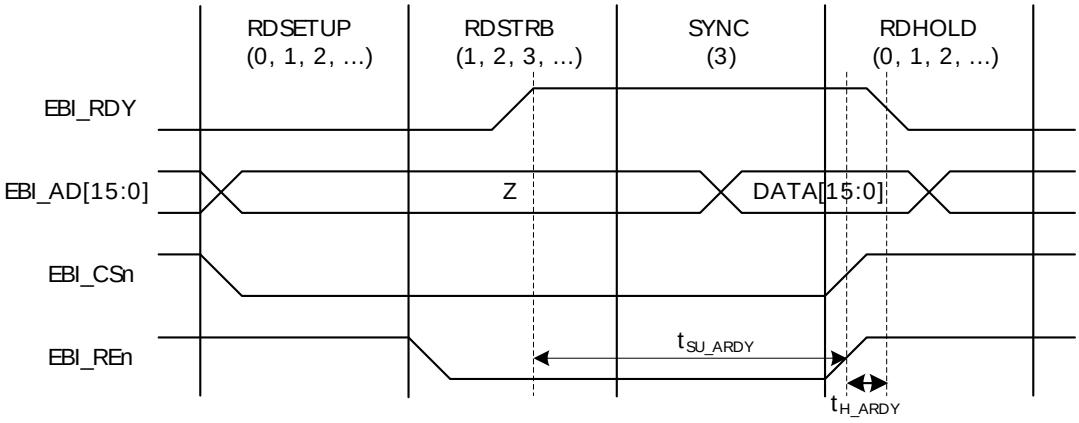


Table 3.23. EBI Ready/Wait Related Timing Requirements

Symbol	Parameter	Min	Typ	Max	Unit
t_{SU_ARDY} [1 2 3 4]	Setup time, from EBI_ARDY valid to trailing EBI_REn, EBI_WEn edge	37 + (3 * $t_{HFCORECLK}$)			ns

Table 3.26. I2C Fast-mode Plus (Fm+)

Symbol	Parameter	Min	Typ	Max	Unit
f_{SCL}	SCL clock frequency	0		1000[1]	kHz
t_{LOW}	SCL clock low time	0.5			µs
t_{HIGH}	SCL clock high time	0.26			µs
$t_{SU,DAT}$	SDA set-up time	50			ns
$t_{HD,DAT}$	SDA hold time	8			ns
$t_{SU,STA}$	Repeated START condition set-up time	0.26			µs
$t_{HD,STA}$	(Repeated) START condition hold time	0.26			µs
$t_{SU,STO}$	STOP condition set-up time	0.26			µs
t_{BUF}	Bus free time between a STOP and START condition	0.5			µs

[1]For the minimum HFPERCLK frequency required in Fast-mode Plus, see the I2C chapter in the EFM32GG Reference Manual.

3.17 USART SPI

Figure 3.36. SPI Master Timing

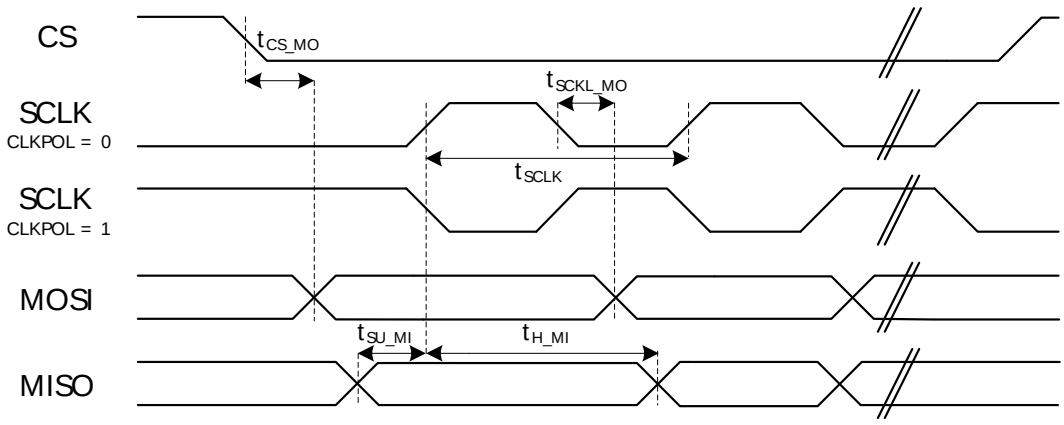


Table 3.27. SPI Master Timing

Symbol	Parameter	Condition	Min	Typ	Max	Unit
t_{SCLK} [1] [2]	SCLK period		2 * $t_{HFPER-CLK}$			ns
t_{CS_MO} [1] [2]	CS to MOSI		-2.00		1.00	ns
t_{SCLK_MO} [1] [2]	SCLK to MOSI		-4.00		3.00	ns
t_{SU_MI} [1] [2]	MISO setup time	IOVDD = 1.98 V	36.00			ns
		IOVDD = 3.0 V	29.00			ns
t_{H_MI} [1] [2]	MISO hold time		-4.00			ns

[1]Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)
[2]Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{TIMER}	TIMER current	TIMER_0 idle current, clock enabled		6.9		µA/MHz
$I_{LETIMER}$	LETIMER current	LETIMER idle current, clock enabled		119		nA
I_{PCNT}	PCNT current	PCNT idle current, clock enabled		54		nA
I_{RTC}	RTC current	RTC idle current, clock enabled		54		nA
I_{AES}	AES current	AES idle current, clock enabled		3.2		µA/MHz
I_{GPIO}	GPIO current	GPIO idle current, clock enabled		3.7		µA/MHz
I_{EBI}	EBI current	EBI idle current, clock enabled		11.8		µA/MHz
I_{PRS}	PRS current	PRS idle current		3.5		µA/MHz
I_{DMA}	DMA current	Clock enable		11.0		µA/MHz

4 Pinout and Package

Note

Please refer to the application note "AN0002 EFM32 Hardware Design Considerations" for guidelines on designing Printed Circuit Boards (PCB's) for the EFM32GG380.

4.1 Pinout

The *EFM32GG380* pinout is shown in Figure 4.1 (p. 53) and Table 4.1 (p. 53). Alternate locations are denoted by "#" followed by the location number (Multiple locations on the same pin are split with "/"). Alternate locations can be configured in the LOCATION bitfield in the *_ROUTE register in the module in question.

Figure 4.1. EFM32GG380 Pinout (top view, not to scale)

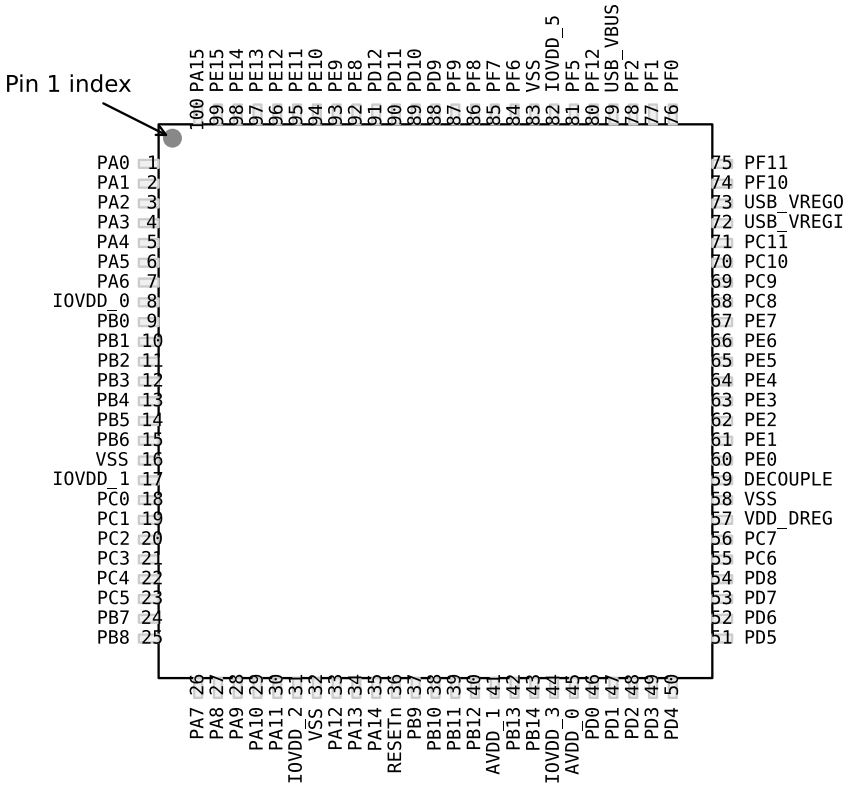


Table 4.1. Device Pinout

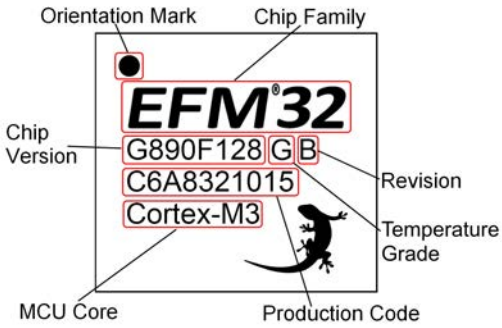
LQFP100 Pin# and Name		Pin Alternate Functionality / Description				
Pin #	Pin Name	Analog	EBI	Timers	Communication	Other
1	PA0		EBI_AD09 #0/1/2	TIM0_CC0 #0/1/4	I2C0_SDA #0 LEU0_RX #4	PRS_CH0 #0 GPIO_EM4WU0
2	PA1		EBI_AD10 #0/1/2	TIM0_CC1 #0/1	I2C0_SCL #0	CMU_CLK1 #0 PRS_CH1 #0
3	PA2		EBI_AD11 #0/1/2	TIM0_CC2 #0/1		CMU_CLK0 #0

6 Chip Marking, Revision and Errata

6.1 Chip Marking

In the illustration below package fields and position are shown.

Figure 6.1. Example Chip Marking (top view)



6.2 Revision

The revision of a chip can be determined from the "Revision" field in Figure 6.1 (p. 69) .

6.3 Errata

Please see the errata document for EFM32GG380 for description and resolution of device erratas. This document is available in Simplicity Studio and online at: http://www.silabs.com/support/pages/document-library.aspx?p=MCUs--32-bit

7 Revision History

7.1 Revision 1.40

March 21st, 2016

Added clarification on conditions for INL_{ADC} and DNL_{ADC} parameters.

Reduced maximum and typical current consumption for all EM0 entries except 48 MHz in the Current Consumption table in the Electrical Characteristics section.

Increased maximum specifications for EM2 current, EM3 current, and EM4 current in the Current Consumption table in the Electrical Characteristics section.

Increased typical specification for EM2 and EM3 current at 85 C in the Current Consumption table in the Electrical Characteristics section.

Added EM2, EM3, and EM4 current consumption vs. temperature graphs.

Added a new EM2 entry and specified the existing specification is for EM0 for the BOD threshold on falling external supply voltage in the Power Management table in the Electrical Characteristics section.

Reduced maximum input leakage current in the GPIO table in the Electrical Characteristics section.

Added a maximum current consumption specification to the LFRCO table in the Electrical Characteristics section.

Added maximum specifications for the active current including references for two channels to the DAC table in the Electrical Characteristics section.

Increased the maximum specification for DAC offset voltage in the DAC table in the Electrical Characteristics section.

Increased the typical specifications for active current with FULLBIAS=1 and capacitive sense internal resistance in the ACMP table in the Electrical Characteristics section.

Added minimum and maximum specifications and updated the typical value for the VCMP offset voltage in the VCMP table in the Electrical Characteristics section.

Removed the maximum specification and reduced the typical value for hysteresis in the VCMP table in the Electrical Characteristics section.

Updated all graphs in the Electrical Characteristics section to display data for 2.0 V as the minimum voltage.

7.2 Revision 1.30

May 23rd, 2014

Removed "preliminary" markings

Updated HFRCO figures.

Corrected single power supply voltage minimum value from 1.85V to 1.98V.

Updated Current Consumption information.

Updated Power Management information.

Updated GPIO information.

Updated LFRCO information.

Updated HFRCO information.

Updated ULFRCO information.

Updated ADC information.

Updated DAC information.

Updated OPAMP information.

Updated ACMP information.

Updated VCMP information.

Added AUXHFRCO information.

7.3 Revision 1.21

November 21st, 2013

Updated figures.

Updated errata-link.

Updated chip marking.

Added link to Environmental and Quality information.

Re-added missing DAC-data.

7.4 Revision 1.20

September 30th, 2013

Added I2C characterization data.

Added SPI characterization data.

Added EBI characterization data.

Corrected the DAC and OPAMP2 pin sharing information in the Alternate Functionality Pinout section.

Corrected GPIO operating voltage from 1.8 V to 1.85 V.

Added the USB bootloader information.

Updated that the EM2 current consumption test was carried out with only one RAM block enabled.

Corrected the ADC resolution from 12, 10 and 6 bit to 12, 8 and 6 bit.

Updated Environmental information.

Updated trademark, disclaimer and contact information.

Other minor corrections.

7.10 Revision 0.91

March 21th, 2011

Added new alternative locations for EBI and SWO.

Added new USB Pin to pinout table.

Corrected slew rate data for Opamps.

7.11 Revision 0.90

February 4th, 2011

Initial preliminary release.

B Contact Information

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Austin, TX 78701

Please visit the Silicon Labs Technical Support web page:
http://www.silabs.com/support/pages/contacttechnicalsupport.aspx
and register to submit a technical support request.

List of Equations